

isc N-Channel MOSFET Transistor

2SK3779-01R

FEATURES

- Drain Current : I_D= 59A@ T_C=25℃
- Drain Source Voltage
 - : V_{DSS}= 250V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)}$ = 53m Ω (Max) @ V_{GS} = 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

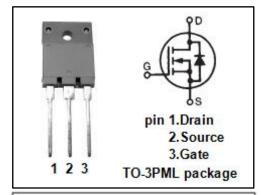
 motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------------|
| V _{DSS} | Drain-Source Voltage | 250 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ±30 | V |
| I _D | Drain Current-Continuous | 59 | А |
| І _{ОМ} | Drain Current-Single Pluse | 236 | А |
| P_D | Total Dissipation @T _C =25℃ | 210 | W |
| TJ | Max. Operating Junction Temperature | -55~150 | $^{\circ}$ |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|-------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.595 | °C/W |



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|------------|--|---|--|---|
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| k ' | . | → R | N-> | D |
| | | m | m | |
| | 2002 | | **** | |
| | DIM | MIN | MAX | |
| | Α | 19.90 | 20.10 | |
| | A B | 19.90 15.75 | 20.10 16.10 | |
| | A B C | 19.90 15.75 5.50 | 20.10 16.10 5.70 | |
| | B C D | 19.90 15.75 5.50 0.90 | 20.10 16.10 5.70 1.10 | |
| | A B C | 19.90 15.75 5.50 | 20.10 16.10 5.70 1.10 3.50 | |
| | B C D | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 | 20.10 16.10 5.70 1.10 | |
| | A B C D F G H | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 | |
| | A B C D F G | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 | |
| | A B C D F G H J K | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 | |
| | A B C D F G H J K L | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 10.80 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 11.00 | |
| | A B C D F G H J K L N O | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 10.80 4.90 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 11.00 5.10 | |
| | B C D F G H J K L N Q R | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 10.80 4.90 3.75 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 11.00 5.10 3.95 | |
| | B C D F G H J K L N Q R S | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 10.80 4.90 3.75 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 11.00 5.10 3.95 3.60 | |
| | B C D F G H J K L N Q R | 19.90 15.75 5.50 0.90 3.30 2.90 5.90 0.595 21.10 1.90 10.80 4.90 3.75 | 20.10 16.10 5.70 1.10 3.50 3.20 6.10 0.70 22.50 2.25 11.00 5.10 3.95 | |

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 250 | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = 10V; I _D = 0.25mA | 3.0 | 5.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 29.5A | | 53 | m Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | ±0.1 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 250V; V _{GS} = 0 | | 25 | uA |
| V _{SD} | Forward On-Voltage | I _S = 59A; V _{GS} = 0 | | 1.5 | V |

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